

**KP979B**

## SILICON MOS N-CHANNEL POWER TRANSISTOR 150 W, up to 230 MHz, Enhancement Mode

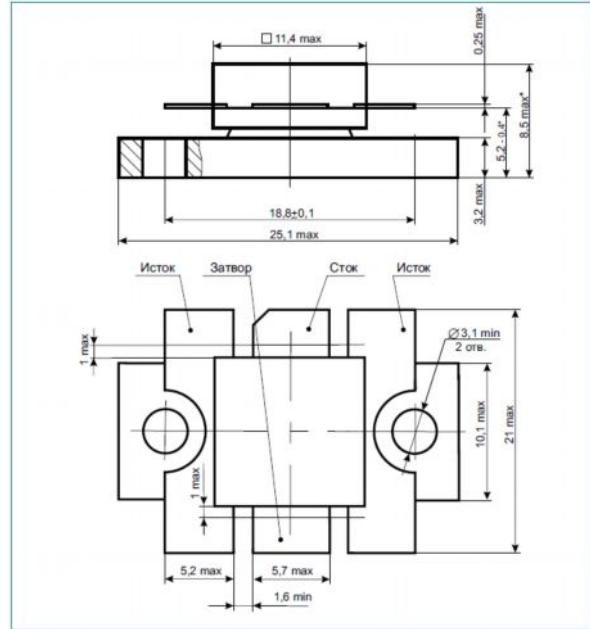
The silicon MOS transistor is designed for professional transmitter applications in the HF/VHF frequency range.

### Features:

- Performance at 230 MHz, 28 Vdc
- Power Gain: 13 dB Min
- Output Power: 150 W
- Efficiency: 50 % Min

### Absolute Maximum Ratings

Parameters	Sym	Value	Unit
Drain-Source Voltage	V <sub>DSS</sub>	65	V <sub>DC</sub>
Drain Current-Continuous	I <sub>D</sub>	17	A <sub>DC</sub>
Gate-Source Voltage	V <sub>GS</sub>	±20	V <sub>DC</sub>
Operation Junction Temperature	T <sub>j</sub>	-65 ÷ +200	°C
Storage Temperature Range	T <sub>STG</sub>	-65 ÷ +150	°C
Thermal Resistance, Junction to Case	R <sub>θJC</sub>	0.85	°C/W
Total Power Dissipation	P <sub>D</sub>	206	W



Case KT-56

### Parameters

Parameter	Symbol	Min.	Typ.	Max.	Unit
Drain-Source Breakdown Voltage (I <sub>DS</sub> =20 mA, V <sub>GS</sub> =0 V)	V <sub>(BR)DSS</sub>	65	—	—	V <sub>DC</sub>
Gate-Source Leakage Current (V <sub>GS</sub> =20 V, V <sub>DS</sub> =0 V)	I <sub>GSS</sub>	—	—	1	μA <sub>DC</sub>
Zero Gate Voltage Drain Leakage Current (V <sub>DS</sub> = 28 V, V <sub>GS</sub> =0 V)	I <sub>DSS</sub>	—	—	10	mA <sub>DC</sub>
Gate Threshold Voltage (V <sub>DS</sub> = 10 V, I <sub>D</sub> = 50mA)	V <sub>GS(TH)</sub>	2	—	5	V <sub>DC</sub>
Forward Transconductance (V <sub>DS</sub> = 10 V, I <sub>D</sub> = 5 A)	G <sub>FS</sub>	2.9	3.2	—	mhos
Input Capacitance (V <sub>DS</sub> = 28 V, V <sub>GS</sub> =0 V, f = 1 MHz)	C <sub>ISS</sub>	—	220	—	pF
Output Capacitance (V <sub>DS</sub> = 28 V, V <sub>GS</sub> =0 V, f = 1 MHz)	C <sub>OSS</sub>	—	190	—	pF
Reverse Transfer Capacitance (V <sub>DS</sub> = 28 V, V <sub>GS</sub> =0 V, f = 1 MHz)	C <sub>RSS</sub>	—	20	—	pF
Power Gain (V <sub>DS</sub> = 28 V, P <sub>OUT</sub> = 150 W, I <sub>DQ</sub> = 100 mA, f = 230 MHz)	G <sub>p</sub>	13	15	—	dB
Drain Efficiency (V <sub>DS</sub> = 28 V, P <sub>OUT</sub> = 150 W, I <sub>DQ</sub> = 100 mA, f = 230 MHz)	η <sub>D</sub>	50	60	—	%

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Specification is subject to change without notice